

# Hoon Ryu

## List of Publications by Year in descending order

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Version: 2024-02-01

26  
papers

1,267  
citations

933447

10  
h-index

794594

19  
g-index

26  
all docs

26  
docs citations

26  
times ranked

1431  
citing authors

#	ARTICLE	IF	CITATIONS
1	Exploring the behaviors of electrode-driven Si quantum dot systems: from charge control to qubit operations. <i>Nanoscale</i> , 2021, 13, 332-339.	5.6	7
2	High Performance Simulations of Quantum Transport using Manycore Computing. , 2021, , .		0
3	Enabling Large-Scale Simulations of Quantum Transport with Manycore Computing. <i>Electronics (Switzerland)</i> , 2021, 10, 253.	3.1	0
4	High-performance simulations of turbulent boundary layer flow using Intel Xeon Phi many-core processors. <i>Journal of Supercomputing</i> , 2021, 77, 9597-9614.	3.6	4
5	Cost-efficient simulations of large-scale electronic structures in the standalone manycore architecture. <i>Computer Physics Communications</i> , 2021, 267, 108078.	7.5	1
6	Enhancing Light-emission Stability of Metal-halide Perovskites with Size and Composition Engineering. <i>Journal of Semiconductor Technology and Science</i> , 2020, 20, 12-18.	0.4	1
7	Role of Quantum Confinement in 10 nm Scale Perovskite Optoelectronics. <i>Journal of Physical Chemistry Letters</i> , 2019, 10, 2745-2752.	4.6	8
8	Acceleration of Large-Scale Electronic Structure Simulations with Heterogeneous Parallel Computing. , 2019, , .		0
9	Cost-efficiency of Large-scale Electronic Structure Simulations with Intel Xeon Phi Processors. , 2019, , .		0
10	Piezoresistivity of InAsP Nanowires: Role of Crystal Phases and Phosphorus Atoms in Strain-Induced Channel Conductances. <i>Molecules</i> , 2019, 24, 3249.	3.8	3
11	Fast, energy-efficient electronic structure simulations for multi-million atomic systems with GPU devices. <i>Journal of Computational Electronics</i> , 2018, 17, 698-706.	2.5	5
12	On the achievement of high fidelity and scalability for large-scale diagonalizations in grid-based DFT simulations. <i>International Journal of Quantum Chemistry</i> , 2018, 118, e25622.	2.0	2
13	Performance Evaluation of Scientific Applications on Intel Xeon Phi Knights Landing Clusters. , 2018, , .		5
14	Optical Properties of Organic Perovskite Materials for Finite Nanostructures. , 2018, , .		0
15	Time-efficient simulations of tight-binding electronic structures with Intel Xeon PhiTM many-core processors. <i>Computer Physics Communications</i> , 2016, 209, 79-87.	7.5	14
16	A multi-subband Monte Carlo study on dominance of scattering mechanisms over carrier transport in sub-10-nm Si nanowire FETs. <i>Nanoscale Research Letters</i> , 2016, 11, 36.	5.7	17
17	Atomistic Study on Dopant-Distributions in Realistically Sized, Highly P-Doped Si Nanowires. <i>Nano Letters</i> , 2015, 15, 450-456.	9.1	12
18	Multimillion-atom modeling of InAs/GaAs quantum dots: interplay of geometry, quantization, atomicity, strain, and linear and quadratic polarization fields. <i>Journal of Computational Electronics</i> , 2015, 14, 543-556.	2.5	7

#	ARTICLE	IF	CITATIONS
19	A Tight-Binding Study of Single-Atom Transistors. <i>Small</i> , 2015, 11, 374-381.	10.0	14
20	Spin blockade and exchange in Coulomb-confined silicon double quantum dots. <i>Nature Nanotechnology</i> , 2014, 9, 430-435.	31.5	117
21	Atomistic modeling of metallic nanowires in silicon. <i>Nanoscale</i> , 2013, 5, 8666.	5.6	28
22	A single-atom transistor. <i>Nature Nanotechnology</i> , 2012, 7, 242-246.	31.5	730
23	Quantitative excited state spectroscopy of a single InGaAs quantum dot molecule through multi-million-atom electronic structure calculations. <i>Nanotechnology</i> , 2011, 22, 315709.	2.6	28
24	Moving Toward Nano-TCAD Through Multimillion-Atom Quantum-Dot Simulations Matching Experimental Data. <i>IEEE Nanotechnology Magazine</i> , 2009, 8, 330-344.	2.0	52
25	Million Atom Electronic Structure and Device Calculations on Peta-Scale Computers. , 2009, , .		11
26	Atomistic Simulation of Realistically Sized Nanodevices Using NEMO 3-Dâ€™Part I: Models and Benchmarks. <i>IEEE Transactions on Electron Devices</i> , 2007, 54, 2079-2089.	3.0	201